

REMARKS/ARGUMENTS

Claims 1, 2, 4 and 12 have been amended. The limitation of forming, within the substrate, a silicon-germanium region in each of the source and drain regions was added to the claims. This limitation finds support in the specification in lines 12-14 and Figure 1. This limitation clearly differentiates the cited prior art references. None of the cited prior art references show a silicon-germanium region being formed "within" the substrate.

In light of the above, it is respectfully submitted that the present application is in condition for allowance, and notice to that effect is respectfully requested.

While it is believed that the instant response places the application in condition for allowance, should the Examiner have any further comments or suggestions, it is respectfully requested that the Examiner contact the undersigned in order to expeditiously resolve any outstanding issues.

To the extent necessary, Applicants petition for an Extension of Time under 37 CFR 1.136. Please charge any fees in connection with the filing of this paper, including extension of time fees, to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.

Respectfully submitted,



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